

FDS4675_F085

40V P-Channel PowerTrench® MOSFET

General Description

This P-Channel MOSFET is a rugged gate version of Fairchild Semiconductor's advanced PowerTrench process. It has been optimized for power management applications requiring a wide range of gate drive voltage ratings (4.5V – 20V).

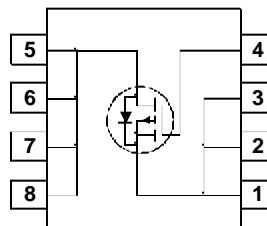
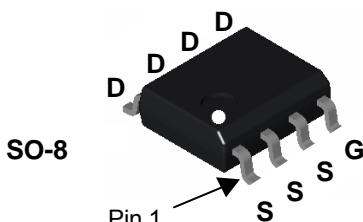
Applications

- Power management
- Load switch
- Battery protection



Features

- -11 A, -40 V $R_{DS(ON)} = 0.013 \Omega$ @ $V_{GS} = -10 \text{ V}$
 $R_{DS(ON)} = 0.017 \Omega$ @ $V_{GS} = -4.5 \text{ V}$
- Fast switching speed
- High performance trench technology for extremely low $R_{DS(ON)}$
- High power and current handling capability
- Qualified to AEC Q101
- RoHS Compliant



Absolute Maximum Ratings

$T_A = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Ratings	Units
V_{DSS}	Drain-Source Voltage	-40	V
V_{GSS}	Gate-Source Voltage	± 20	V
I_D	Drain Current – Continuous (Note 1a)	-11	A
	– Pulsed	-50	
P_D	Power Dissipation for Single Operation (Note 1a)	2.4 (steady state)	W
	(Note 1b)	1.4	
	(Note 1c)	1.2	
T_J, T_{STG}	Operating and Storage Junction Temperature Range	-55 to +175	°C

Thermal Characteristics

$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient (Note 1a)	62.5 (steady state), 50 (10 sec)	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient (Note 1c)	125	°C/W
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case (Note 1)	25	°C/W

Package Marking and Ordering Information

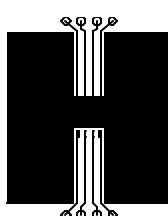
Device Marking	Device	Reel Size	Tape width	Quantity
FDS4675	FDS4675_F085	13"	12mm	2500 units

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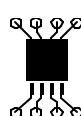
Electrical Characteristics						
Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
Off Characteristics						
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS} = 0 \text{ V}$, $I_D = -250 \mu\text{A}$	-40			V
ΔBV_{DSS} ΔT_J	Breakdown Voltage Temperature Coefficient	$I_D = -250 \mu\text{A}$, Referenced to 25°C		-34		mV/°C
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = -32 \text{ V}$, $V_{GS} = 0 \text{ V}$		-1		μA
I_{GSSF}	Gate-Body Leakage, Forward	$V_{GS} = 20 \text{ V}$, $V_{DS} = 0 \text{ V}$		100		nA
I_{GSSR}	Gate-Body Leakage, Reverse	$V_{GS} = -20 \text{ V}$, $V_{DS} = 0 \text{ V}$		-100		nA
On Characteristics (Note 2)						
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}$, $I_D = -250 \mu\text{A}$	-1	-1.4	-3	V
$\Delta V_{GS(th)}$ ΔT_J	Gate Threshold Voltage Temperature Coefficient	$I_D = -250 \mu\text{A}$, Referenced to 25°C		4.6		mV/°C
$R_{DS(on)}$	Static Drain-Source On-Resistance	$V_{GS} = -10 \text{ V}$, $I_D = -11 \text{ A}$ $V_{GS} = -4.5 \text{ V}$, $I_D = -9.5 \text{ A}$ $V_{GS} = -10 \text{ V}$, $I_D = -11 \text{ A}$, $T_J = 125^\circ\text{C}$	10 13 15	13 17 21		$\text{m}\Omega$
$I_{D(on)}$	On-State Drain Current	$V_{GS} = -10 \text{ V}$, $V_{DS} = -5 \text{ V}$	-25			A
g_{FS}	Forward Transconductance	$V_{DS} = -5 \text{ V}$, $I_D = -11 \text{ A}$		44		S
Dynamic Characteristics						
C_{iss}	Input Capacitance	$V_{DS} = -20 \text{ V}$, $V_{GS} = 0 \text{ V}$, $f = 1.0 \text{ MHz}$		4350		pF
C_{oss}	Output Capacitance			622		pF
C_{rss}	Reverse Transfer Capacitance			290		pF
Switching Characteristics (Note 2)						
$t_{d(on)}$	Turn-On Delay Time	$V_{DD} = -20 \text{ V}$, $I_D = -1 \text{ A}$, $V_{GS} = -4.5 \text{ V}$, $R_{GEN} = 6 \Omega$		20	36	ns
t_r	Turn-On Rise Time			29	46	ns
$t_{d(off)}$	Turn-Off Delay Time			95	152	ns
t_f	Turn-Off Fall Time			60	96	ns
Q_g	Total Gate Charge	$V_{DS} = -20 \text{ V}$, $I_D = -11 \text{ A}$, $V_{GS} = -4.5 \text{ V}$		40	56	nC
Q_{gs}	Gate-Source Charge			11		nC
Q_{gd}	Gate-Drain Charge			13		nC
Drain-Source Diode Characteristics and Maximum Ratings						
I_S	Maximum Continuous Drain-Source Diode Forward Current			-2.1		A
V_{SD}	Drain-Source Diode Forward Voltage	$V_{GS} = 0 \text{ V}$, $I_S = -2.1 \text{ A}$ (Note 2)		-0.7	-1.2	V

Notes:

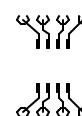
1. R_{thJA} is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. R_{thJC} is guaranteed by design while R_{thCA} is determined by the user's board design.



a) 50°C/W when mounted on a 1in² pad of 2 oz copper



b) 105°C/W when mounted on a .04 in² pad of 2 oz copper



c) 125°C/W when mounted on a minimum pad.

Scale 1 : 1 on letter size paper

2. Pulse Test: Pulse Width < 300μs, Duty Cycle < 2.0%

Typical Characteristics

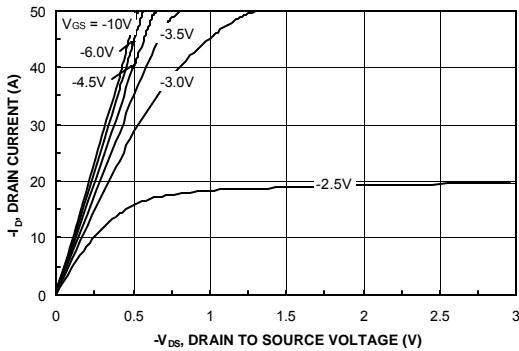


Figure 1. On-Region Characteristics.

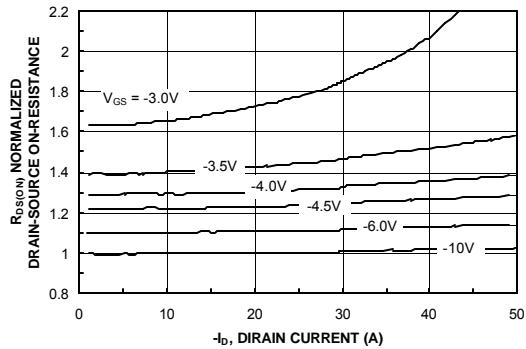


Figure 2. On-Resistance Variation with Drain Current and Gate Voltage.

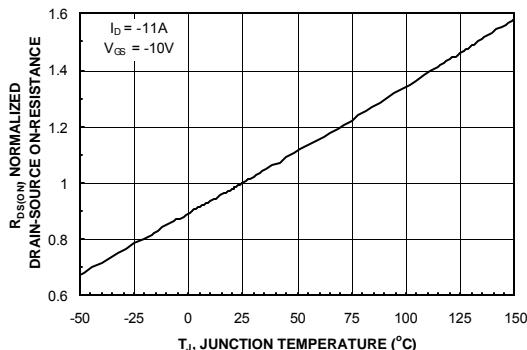


Figure 3. On-Resistance Variation with Temperature.

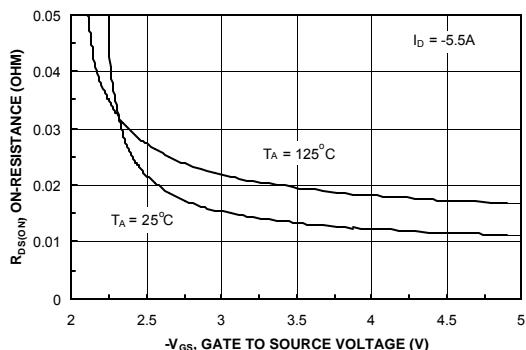


Figure 4. On-Resistance Variation with Gate-to-Source Voltage.

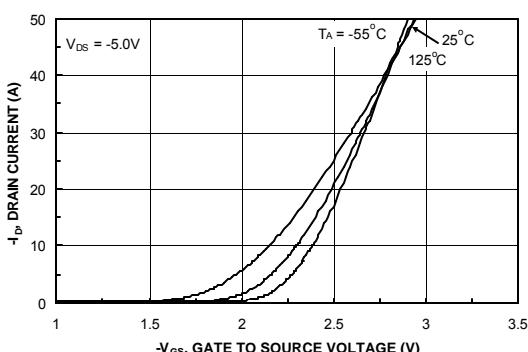


Figure 5. Transfer Characteristics.

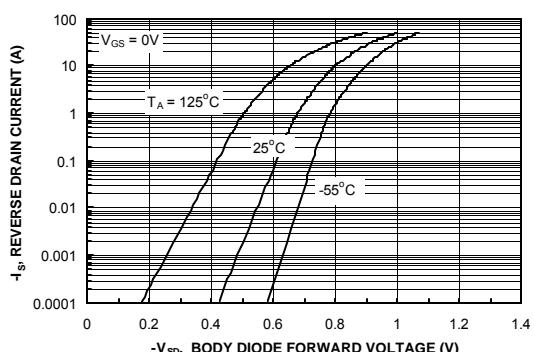


Figure 6. Body Diode Forward Voltage Variation with Source Current and Temperature.

Typical Characteristics

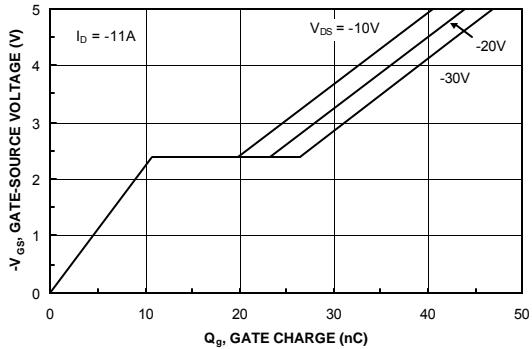


Figure 7. Gate Charge Characteristics.

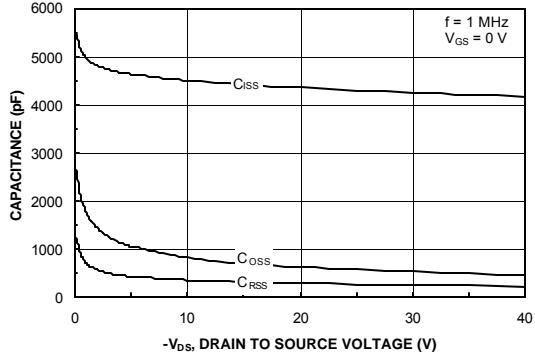


Figure 8. Capacitance Characteristics.

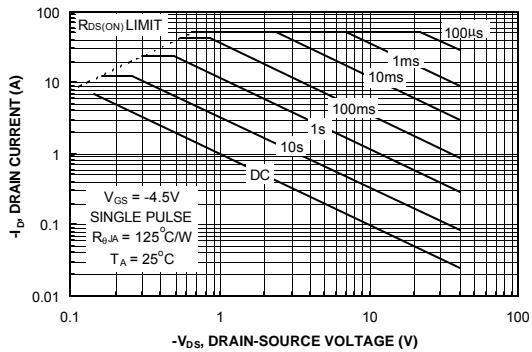


Figure 9. Maximum Safe Operating Area.

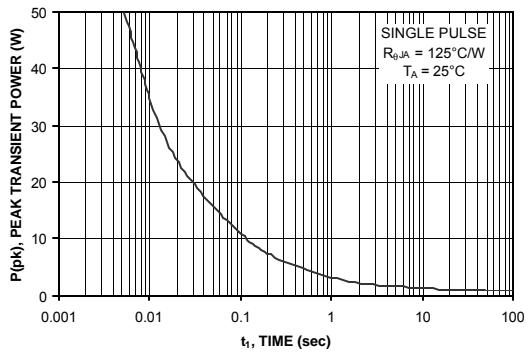


Figure 10. Single Pulse Maximum Power Dissipation.

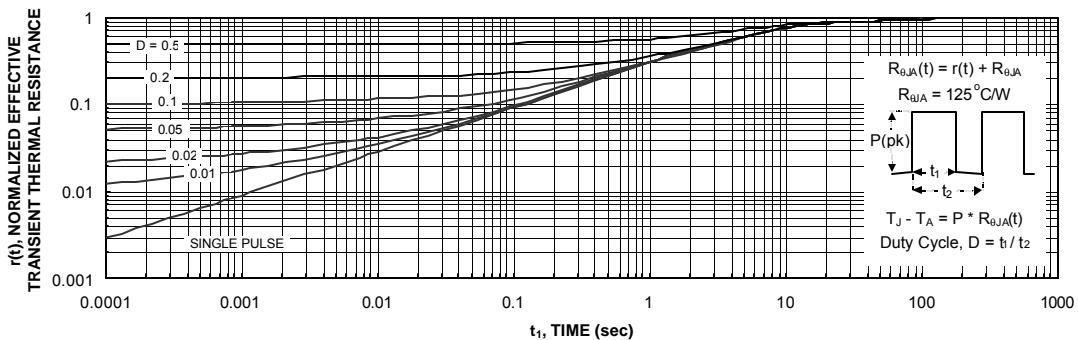


Figure 11. Transient Thermal Response Curve.

Thermal characterization performed using the conditions described in Note 1c.
Transient thermal response will change depending on the circuit board design.

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